PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
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EPAS ID: PAT3635870

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
NXP B.V.	09/04/2015

RECEIVING PARTY DATA

Name:	SAMBA HOLDCO NETHERLANDS B.V.
Street Address:	HIGH TECH CAMPUS 60
City:	EINDHOVEN
State/Country:	NETHERLANDS
Postal Code:	5656 AG

PROPERTY NUMBERS Total: 22

Property Type	Number
Patent Number:	5681761
Patent Number:	6235601
Patent Number:	6917077
Patent Number:	6646321
Patent Number:	6990323
Patent Number:	7119613
Patent Number:	7119623
Patent Number:	7138872
Patent Number:	7078976
Patent Number:	7482873
Patent Number:	7157974
Patent Number:	7332961
Patent Number:	7286016
Patent Number:	7477106
Patent Number:	7392023
Patent Number:	7483681
Patent Number:	8357979
Patent Number:	7443264
Patent Number:	7521768
Patent Number:	7884668

Property Type	Number
Patent Number:	7873335
Application Number:	14054681

CORRESPONDENCE DATA

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NAME OF SUBMITTER:	VILIMAINA NAGA
SIGNATURE:	/Vilimaina Naga/
DATE SIGNED:	11/30/2015

Total Attachments: 8
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DEED OF TRANSFER

Form of Deed of Transfer of Patents

THE UNDERSIGNED:

(1) **NXP B.V.**, a private limited liability company incorporated under the laws of the Netherlands, with corporate seat in Eindhoven, the Netherlands, and address at High Tech Campus 60, 5656AG Eindhoven, ("**NXP**");

and

(2) **Samba Holdco Netherlands B.V.**, a private limited liability company incorporated under the laws of the Netherlands, with corporate seat in Eindhoven, the Netherlands, and address at High Tech Campus 60, 5656 AG Eindhoven, (the "**Assignee**");

together also to be referred to as "**Parties**" and each party individually as a "**Party**", as the case may be.

WHEREAS:

(A) The Parties have entered into a patent sale and purchase agreement on 4th September 2015 relating to the sale and purchase of certain patents by NXP to the Assignee (the "**Agreement**");

(B) Pursuant to the Agreement, NXP has sold the legal title to the patents identified in Schedule A to this Deed (the "**Transferred Patents**") to the Assignee and has agreed to transfer the legal title to the Transferred Patents to the Assignee in this Deed; and

(C) The Parties hereby wish to transfer the legal title to the Transferred Patents to the Assignee on the terms and conditions as set out in this Deed.

HAVE AGREED AS FOLLOWS:

1. **Definitions**

When used in this Deed, the following capitalized terms shall have the meaning set forth below:

"**Agreement**" has the meaning set out in the preamble;

"**Deed**" means this deed of transfer including the Schedule;

"**Party**" and "**Parties**" has the meaning set out in the introduction;

"**Schedule**" means the schedule to this Deed; and

"**Transferred Patents**" has the meaning set out in the preamble.

2. **Transfer of ownership of the Transferred Patents**

NXP hereby assigns, transfers and conveys its legal title to the Transferred Patents to the Assignee, and the Assignee hereby accepts from NXP such assignment, transfer and conveyance. NXP authorizes and requests the patent register (including any applicable foreign or international office or register) to record the Assignee as the legal owner of the Transferred Patents, and as assignee of NXP's legal title to the same.

3. **Variation to the Deed**

No variation, extension, cancellation or translation of any expressed terms of this Deed (including in Schedule A) shall be binding upon NXP or the Assignee unless made in writing and signed by duly authorized representatives of NXP and the Assignee.

4. **Additional assignment documents; further assurance**

The Assignee will be responsible for effectuating the recordation of the assignment and transfer of the Transferred Patents listed in Schedule A. NXP and the Assignee shall, at each other's request, and without further consideration, execute and do all such deeds, documents, acts and things as the requesting party may from time to time reasonably require in order to effectuate or to formalize the transfer of the Transferred Patents to the Assignee on a jurisdiction by jurisdiction basis and to cause the Transferred Patents to be recorded at the relevant patent registers around the world in the name of the Assignee.

5. **Observance legal requirements**

The Assignee and NXP undertake to observe and act in accordance with all applicable legal conditions and terms required in order to effectuate the recordation of the assignment and transfer of the Transferred Patents in the relevant registers.

6. **Costs for recordation**

The costs for the recordation of the assignment and transfer of the Transferred Patents in the relevant registers shall be borne by the Assignee.

7. **Applicable law and jurisdiction**

This Deed shall be governed by and construed in accordance with the laws of the Netherlands. Any action or proceeding in respect of any claim arising out of or related to this Deed shall be solely conducted by NXP and the Assignee in accordance with the dispute settlement procedure provided in the SPA.

8. **No rescission and no nullification**

Each Party waives its right to rescind (*ontbinden*) this Deed on the basis of section 6:265 of the Netherlands Civil Code.

IN EVIDENCE WHEREOF, the Parties have caused this Deed to be signed by their duly authorized representatives effective as of 4th September 2015.

NXP B.V.

(signature)

Name: John Schmitz

Title: CIPO

Samba Holdco Netherlands B.V.

(signature)

Name: Jean Schreurs

Title: Authorized Signatory

Schedule A: Transferred Patents

Schedule A - Transferred Patents

NXP Reference	Status	Title	Region	PriorityDate	FiledDate	ApplicationNumber	PublicationNumber	PatentNumber
000372CN	Granted	A fast and power-efficient supply modulator for RF power	CN	2005-04-20	2006-04-12	200680013269.7	CN101164227	CN200680013269
000372US	Granted	A fast and power-efficient supply modulator for RF power	US	2005-04-20	2006-04-12	11/911699	US20080252380	US8035362
000489CN1	Granted	bias circuit with reduced parameter spread	CN	2005-05-26	2006-05-11	200680018001.2	CN101180729	CN200680018001
000489DE02	Granted	bias circuit with reduced parameter spread	DE	2005-05-26	2006-05-11	06744913.2		DE602006034911
000489IN1	Published	bias circuit with reduced parameter spread	IN	2005-05-26	2006-05-11	9992/DELNP/2007	9992/DELNP/2007	
000489JP1	Granted	bias circuit with reduced parameter spread	JP	2005-05-26	2006-05-11	2008-512974		JP4964875
000489TW1	Granted	bias circuit with reduced parameter spread	TW	2005-05-26	2006-05-23	095118271		TWI404191
000489US1	Granted	bias circuit with reduced parameter spread	US	2005-05-26	2006-05-11	11/915464	US20100252865	US7948014
001408CN	Granted	Sensing and Correction of Differential Path Delay in	CN	2005-07-27	2006-07-26	200680027410.9	CN101233681	CN200680027410
001408DE	Granted	Sensing and Correction of Differential Path Delay in	DE	2005-07-27	2006-07-26	06780211.6		DE602006020734
001408FR	Granted	Sensing and Correction of Differential Path Delay in	FR	2005-07-27	2006-07-26	06780211.6		FR1911153
001408US1	Granted	Sensing and Correction of Differential Path Delay in	US	2005-07-27	2006-07-26	11/996329	US20080242246	US7970362
001766CN1	Granted	Local thick thermal-oxide to reduce hot carrier	CN	2005-07-13	2006-07-10	200680025346.0	CN101218682	CN200680025346
001766EP2	Published	Local thick thermal-oxide to reduce hot carrier	EP	2005-07-13	2006-07-10	06766058.9	EP1905098	
001766JP1	Granted	Local thick thermal-oxide to reduce hot carrier	JP	2005-07-13	2006-07-10	521012/2008		JP5215849
001766KR1	Granted	Local thick thermal-oxide to reduce hot carrier	KR	2005-07-13	2006-07-10	2008-7003389	KR20080033395	KR0976662
001766US1	Granted	Local thick thermal-oxide to reduce hot carrier	US	2005-07-13	2006-07-10	11/995087	US20090218622	US7989879
002312CN1	Granted	Multi-path LDMOS using p-type epitaxy	CN	2005-11-02	2006-10-27	200680040545.9	CN101300679	CN200680040545
002312DE03	Granted	Multi-path LDMOS using p-type epitaxy	DE	2005-11-02	2006-10-27	06809727.8		DE602005033621
002312FR02	Granted	Multi-path LDMOS using p-type epitaxy	FR	2005-11-02	2006-10-27	06809727.8		FR1946378
002312GB04	Granted	Multi-path LDMOS using p-type epitaxy	GB	2005-11-02	2006-10-27	06809727.8		GB1946378
002818CN	Granted	F-class amplification with wide dynamic range	CN	2006-02-10	2007-02-06	200780004828.2	CN101379696	CN200780004828
002818DE03	Granted	F-class amplification with wide dynamic range	DE	2006-02-10	2007-02-06	07705802.2	EP1985012	DE602007015505
002818FR02	Granted	F-class amplification with wide dynamic range	FR	2006-02-10	2007-02-06	07705802.2		FR1985012
002818US1	Granted	F-class amplification with wide dynamic range	US	2006-02-10	2007-02-06	12/278836	US20100164632	US7920029
004436US1	Granted	staircase shield for ldmost	US	2005-12-14	2006-12-12	12/097582	US20080308862	US7576387
004544DE	Granted	RF amplifier with APCA architecture	DE	2004-12-14	2005-12-13	05850863.1		DE602005016461
004544FR	Granted	RF amplifier with APCA architecture	FR	2004-12-14	2005-12-13	05850863.1		FR1829154
004544GB	Granted	RF amplifier with APCA architecture	GB	2004-12-14	2005-12-13	05850863.1		GB1829154
005277CN	Granted	Integrated Doherty Amplifier	CN	2006-04-14	2007-04-11	200780013357.1	CN101421916	CN200780013357
005277DE03	Granted	Integrated Doherty Amplifier	DE	2006-04-14	2007-04-11	07735470.2	EP2011230	DE602007016977
005277FR02	Granted	Integrated Doherty Amplifier	FR	2006-04-14	2007-04-11	07735470.2		FR2011230
005277US1	Granted	Integrated Doherty Amplifier	US	2006-04-14	2007-04-11	12/297036	US20090179702	US7800448
005278CN	Granted	Very high power RF device arrangement with low	CN	2006-04-26	2007-04-24	200780014952.7	CN101617403	CN200780014952
005278EP2	Published	Very high power RF device arrangement with low	EP	2006-04-26	2007-04-24	07735617.8	EP2013943	
005278US1	Granted	Very high power RF device arrangement with low	US	2006-04-26	2007-04-24	12/298735	US20090174482	US7898338
005213JP1	Granted	Optimal thermal design for RF power amplifier	JP	2006-06-20	2007-06-15	2009-516034		JP5060550
005213US1	Granted	Optimal thermal design for RF power amplifier	US	2006-06-20	2007-06-15	12/305693	US20100059879	US8067840
006976CN03	Granted	Backside metallisation with NiAg stack	CN	2006-09-18	2007-09-17	200780034451.5	CN101517719	CN200780034451
006976US01	Granted	Backside metallisation with NiAg stack	US	2006-09-18	2007-09-17	12/441769	US20090267232	US8138087
008053US	Published	3 Way high power Doherty amplification system for	US	2007-09-03	2008-09-02	12/675849	US20100188147	
008054CN	Granted	WiMAX/WCDMA integrated linearized Doherty Amplifier	CN	2007-08-29	2008-08-22	200880104302.6	CN101785177	CN200880104302
008054DE07	Granted	WiMAX/WCDMA integrated linearized Doherty Amplifier	DE	2007-08-29	2008-08-22	08807413.3		DE602008020656
008054FR06	Granted	WiMAX/WCDMA integrated linearized Doherty Amplifier	FR	2007-08-29	2008-08-22	08807413.3		FR2195921
008054GB08	Granted	WiMAX/WCDMA integrated linearized Doherty Amplifier	GB	2007-08-29	2008-08-22	08807413.3		GB2195921
008054US	Granted	WiMAX/WCDMA integrated linearized Doherty Amplifier	US	2007-08-29	2008-08-21	12/674906	US20110204980	US8228123
81049475EP04	Published	VSWR Compensation Circuits For RF Transmit Chain	EP	2008-07-23	2009-07-22	09786680.0	EP2308170	
81049475US05	Granted	VSWR Compensation Circuits For RF Transmit Chain	US	2008-07-23	2009-07-22	13/054798	US20110130104	US8180306
81057467DE07	Granted	Power LDMOS transistor	DE	2008-04-15	2009-04-15	09733241.5		DE602009004921
81057467FR06	Granted	Power LDMOS transistor	FR	2008-04-15	2009-04-15	09733241.5		FR2269219
81057467GB08	Granted	Power LDMOS transistor	GB	2008-04-15	2009-04-15	09733241.5		GB2269219
81057467US05	Granted	Power LDMOS transistor	US	2008-04-15	2009-04-15	12/937701	US20110024835	US8629495
81058083CN03	Granted	Improved Outphasing system	CN	2008-01-29	2009-01-27	200980103322.6	CN101926089	CN200980103322
81058083DE07	Granted	Improved Outphasing system	DE	2008-01-29	2009-01-27	09705153.6		DE602009002701
81058083FR06	Granted	Improved Outphasing system	FR	2008-01-29	2009-01-27	09705153.6		FR2238684
81058083US05	Granted	Improved Outphasing system	US	2008-01-29	2009-01-27	12/864097	US20100295610	US7994854
81338995CN03	Granted	Switching-mode Class-DE Power Amplifier for Out-	CN	2008-05-05	2009-04-30	200980116132.8	CN102017400	CN200980116132
81338995DE07	Granted	Switching-mode Class-DE Power Amplifier for Out-	DE	2008-05-05	2009-04-30	09742499.8		DE602009009497
81338995FR06	Granted	Switching-mode Class-DE Power Amplifier for Out-	FR	2008-05-05	2009-04-30	09742499.8		FR2274829
81338995US05	Granted	Switching-mode Class-DE Power Amplifier for Out-	US	2008-05-05	2009-04-30	12/989890	US20110051842	US8269555
81339831CN03	Granted	Transformer-based power combining and interpolating for digitally envelope-modulated ampifiers or direct RF	CN	2008-03-10	2009-03-09	200980108176.6	CN102007699	CN200980108176
81339831DE07	Granted	Transformer-based power combining and interpolating for digitally envelope-modulated ampifiers or direct RF	DE	2008-03-10	2009-03-09	09720581.9		DE602009002945
81339831FR06	Granted	Transformer-based power combining and interpolating for digitally envelope-modulated ampifiers or direct RF	FR	2008-03-10	2009-03-09	09720581.9		FR2266208
81339831US05	Granted	Transformer-based power combining and interpolating for digitally envelope-modulated ampifiers or direct RF	US	2008-03-10	2009-03-09	12/921572	US20110050344	US8237503
81346526CN03	Granted	A Novel Three-way Doherty Concept	CN	2007-12-21	2008-12-18	200880120959.1	CN101904089	CN200880120959
81346526DE09	Granted	A Novel Three-way Doherty Concept	DE	2007-12-21	2008-12-18	08864796.1		DE602008027216
81346526FR08	Granted	A Novel Three-way Doherty Concept	FR	2007-12-21	2008-12-18	08864796.1		FR2235820
81346526JP05	Granted	A Novel Three-way Doherty Concept	JP	2007-12-21	2008-12-18	2010-539023		JP5001435
81346526KR06	Granted	A Novel Three-way Doherty Concept	KR	2007-12-21	2008-12-18	2010-7016305	KR20100094589	KR1107827
81346526US07	Granted	A Novel Three-way Doherty Concept	US	2007-12-21	2008-12-18	12/809757	US20100315162	US8022760
81346632CN03	Granted	Ruggedness improvement LDMOS by fieldplate design	CN	2008-07-22	2009-07-20	200980128532.0	CN102099920	CN200980128532
81346632DE07	Granted	Ruggedness improvement LDMOS by fieldplate design	DE	2008-07-22	2009-07-20	09786646.1		DE602009022636
81346632FR06	Granted	Ruggedness improvement LDMOS by fieldplate design	FR	2008-07-22	2009-07-20	09786646.1		FR2321850
81346632US05	Granted	Ruggedness improvement LDMOS by fieldplate design	US	2008-07-22	2009-07-20	13/054647	US20110121389	US8450802
81347991CH07	Granted	High power Integrated Doherty Amplifier scalable solution for low frequency band / 1GHz/ based on FET /	CH	2010-11-29	2010-11-29	10252022.8		CH2458730
81347991CN02	Granted	High power Integrated Doherty Amplifier scalable solution for low frequency band / 1GHz/ based on FET /	CN	2010-11-29	2011-11-28	201110384941.6	CN102480272	CN201110384941
81347991DE05	Granted	High power Integrated Doherty Amplifier scalable solution for low frequency band / 1GHz/ based on FET /	DE	2010-11-29	2010-11-29	10252022.8		DE602010007554
81347991FR04	Granted	High power Integrated Doherty Amplifier scalable solution for low frequency band / 1GHz/ based on FET /	FR	2010-11-29	2010-11-29	10252022.8		FR2458730
81347991GB06	Granted	High power Integrated Doherty Amplifier scalable solution for low frequency band / 1GHz/ based on FET /	GB	2010-11-29	2010-11-29	10252022.8		GB2458730
81347991US03	Granted	High power Integrated Doherty Amplifier scalable solution for low frequency band / 1GHz/ based on FET /	US	2010-11-29	2011-11-22	13/302925	US20120133442	US8487703
81348450DE06	Granted	High resolution digital Bandpass RF PWM/PPM modulator	DE	2008-03-31	2009-03-27	09727361.9		DE602009009719
81348450FR05	Granted	High resolution digital Bandpass RF PWM/PPM modulator	FR	2008-03-31	2009-03-27	09727361.9		FR2263355
81348450US04	Granted	High resolution digital Bandpass RF PWM/PPM modulator	US	2008-03-31	2009-03-27	12/934346	US20110044404	US8416880
81349845CN03	Granted	Variable duty cycle generation with accurate phase information for out-phasing and PWM power amplifier	CN	2008-11-10	2009-11-06	200980144745.2	CN102210096	CN200980144745
81349845DE07	Granted	Variable duty cycle generation with accurate phase information for out-phasing and PWM power amplifier	DE	2008-11-10	2009-11-06	09759810.6		DE602009012690
81349845FR06	Granted	Variable duty cycle generation with accurate phase information for out-phasing and PWM power amplifier	FR	2008-11-10	2009-11-06	09759810.6		FR2345155

Schedule A - Transferred Patents

81349845GB08	Granted	Variable duty cycle generation with accurate phase information for out-phasing and PWM power amplifier	GB	2008-11-10	2009-11-06	09759810.6		GB2345155
81349845US05	Granted	Variable duty cycle generation with accurate phase information for out-phasing and PWM power amplifier	US	2008-11-10	2009-11-06	13/128197	US20110216818	US8570101
81349923US05	Granted	Digital Protection and Impedance Mismatch Recording Concept for Low Breakdown Voltage Power Amplifiers	US	2008-12-31	2009-12-11	13/142029	US20110254630	US8373507
81355884DE06	Granted	Stability control of a RF power amplifier	DE	2009-02-25	2010-01-21	10702760.9		DE602010011701
81355884FR05	Granted	Stability control of a RF power amplifier	FR	2009-02-25	2010-01-21	10702760.9		FR2401812
81355884US04	Granted	Stability control of a RF power amplifier	US	2009-02-25	2010-01-21	13/202922	US20120038415	US8319546
81359474CN03	Granted	A new pre-driver with switch power loss elimination and	CN	2008-12-24	2009-11-30	200980151885.2	CN102265511	CN200980151885
81359474DE06	Granted	A new pre-driver with switch power loss elimination and	DE	2008-12-24	2009-11-30	09774963.4		DE602009024945
81359474US05	Granted	A new pre-driver with switch power loss elimination and	US	2008-12-24	2009-11-30	13/141719	US20110260791	US8373508
81363056US04	Granted	Quadrature PWM transmitter concept.	US	2008-11-18	2009-11-02	13/129573	US20110285471	US8766738
81374156CN02	Granted	Invention Disclosure of the Shield on Gate layout for	CN	2010-04-29	2011-04-28	201110112954.8	CN102237410	CN201110112954
81374156EP01	Published	Semiconductor transistor comprising two electrically conductive shield elements	EP		2010-04-29	10161399.0	EP2383786	
81374156US03	Granted	SEMICONDUCTOR TRANSISTOR COMPRISING TWO	US	2010-04-29	2011-04-25	13/093091	US20110266619	US8502311
81377572DE05	Granted	High efficiency Integrated linear device	DE	2009-12-15	2009-12-15	09179345.5		DE602009013414
81377572FR04	Granted	High efficiency Integrated linear device	FR	2009-12-15	2009-12-15	09179345.5		FR2339746
81377572US03	Granted	High efficiency Integrated linear device	US	2009-12-15	2010-12-14	12/967084	US20110140783	US8253494
81377743CN02	Granted	High efficiency power device with internal dynamic bias	CN	2009-12-15	2010-12-14	201010593121.3	CN102098006	CN201010593121
81377743US03	Granted	High efficiency power device with internal dynamic bias	US	2009-12-15	2010-12-14	12/967912	US20110140786	US8482353
81378162US01	Granted	RADIO FREQUENCY AMPLIFIER WITH EFFECTIVE DECOUPLING	US		2009-12-18	12/641817	US20110148529	US7986184
81379235DE04	Granted	A pulse-width modulated class E power amplifier with a variable series inductor whose inductance value varies with the pulse width of the drive to enable high efficiency	DE	2009-09-07	2009-09-07	09252142.6		DE602009007688
81379235FR03	Granted	A pulse-width modulated class E power amplifier with a variable series inductor whose inductance value varies with the pulse width of the drive to enable high efficiency	FR	2009-09-07	2009-09-07	09252142.6		FR2293438
81379235US02	Granted	A SWITCHING AMPLIFIER	US	2009-09-07	2010-09-03	12/875928	US20110057726	US8174311
81387290US01	Granted	SYSTEM AND METHOD FOR COMPENSATING FOR CHANGES IN AN OUTPUT IMPEDANCE OF A POWER	US		2010-06-08	12/796559	US20110298535	US8416023
81388679CN02	Granted	Hybrid for Silicon LDMOS Substrate and Integrated Power	CN	2010-06-01	2011-05-30	201110143025.3	CN102299686	CN201110143025
81388679EP03	Published	Hybrid for Silicon LDMOS Substrate and Integrated Power	EP	2010-06-01	2011-05-27	11167889.2	EP2393112	
81388679US01	Granted	Inductive Circuit Arrangement	US		2010-06-01	12/791589	US20110291772	US8410853
81388946CN02	Granted	Bond Wire Configuration allowing Compact High-Q	CN	2010-06-01	2011-05-30	201110142996.6	CN102332438	CN201110142996
81388946DE05	Granted	Bond Wire Configuration allowing Compact High-Q	DE	2010-06-01	2011-05-31	11168190.4		DE602011002508
81388946FR04	Granted	Bond Wire Configuration allowing Compact High-Q	FR	2010-06-01	2011-05-31	11168190.4		FR2393111
81388946GB06	Granted	Bond Wire Configuration allowing Compact High-Q	GB	2010-06-01	2011-05-31	11168190.4		GB2393111
81388946US01	Granted	Inductive Bond-Wire Circuit	US		2010-06-01	12/791575		US7939864
81393938CN02	Granted	Load modulation PA's with extended broadband	CN	2010-04-23	2011-04-25	201110107268.1	CN102237852	CN201110107268
81393938DE05	Granted	POWER AMPLIFIER	DE	2010-04-23	2010-04-23	10250822.3		DE602010008599
81393938FR04	Granted	POWER AMPLIFIER	FR	2010-04-23	2010-04-23	10250822.3		FR2383883
81393938US03	Granted	POWER AMPLIFIER	US	2010-04-23	2011-04-19	13/089789	US20120126890	US8564367
81394068CN03	Granted	POWER CONTROL OF RECONFIGURABLE OUTPHASING	CN	2010-05-04	2011-05-03	201110115715.8	CN102237853	CN201110115715
81394068DE06	Granted	POWER CONTROL OF RECONFIGURABLE OUTPHASING	DE	2010-05-04	2011-05-03	11164673.3		DE602011003813
81394068FR05	Granted	POWER CONTROL OF RECONFIGURABLE OUTPHASING	FR	2010-05-04	2011-05-03	11164673.3		FR2388912
81394068GB07	Granted	POWER CONTROL OF RECONFIGURABLE OUTPHASING	GB	2010-05-04	2011-05-03	11164673.3		GB2388912
81394068US01	Granted	RECONFIGURABLE OUTPHASING CHIREIX AMPLIFIERS	US		2010-05-04	12/773498	US20110273234	US8203386
81394068US02	Granted	POWER CONTROL OF RECONFIGURABLE OUTPHASING	US	2010-05-04	2010-05-04	13/052722	US20110273236	US8174322
81395404CN02	Granted	Layout of arrayed RF-power transistors with matching circuit included on the area of the RF-power transistor	CN	2011-01-05	2011-12-28	201110447041.1	CN102593120	CN201110447041
81395404EP01	Published	Layout of arrayed RF-power transistors with matching circuit included on the area of the RF-power transistor	EP		2011 01 05	11150247.2	EP2475007	
81395404US03	Granted	Layout of arrayed RF-power transistors with matching circuit included on the area of the RF-power transistor	US	2011-01-05	2011-12-22	13/334637	US20120168840	US8766427
81396335EP01	Published	Partly-matched power RF- LDMOS transistor	EP		2010-11-29	10192922.2	EP2458636	
81396335US02	Granted	Partly-matched power RF- LDMOS transistor	US	2010-11-29	2011-11-23	13/304215	US20120132969	US8981433
81396600CN02	Granted	A two-stage Doherty main power amplifier design for	CN	2010-06-02	2011-06-01	201110145928.5	CN102270966	CN201110145928
81396600US03	Granted	A two-stage Doherty main power amplifier design for	US	2010-06-02	2011-06-01	13/150916	US20110298544	US8390381
81397638CN03	Granted	Bondwire transformers and their application as power	CN	2010-12-14	2011-12-05	201110433085.9	CN102543385	CN201110433085
81397638DE05	Allowed	Bondwire transformers and their application as power	DE	2010-12-03	2010-12-14	10194851.1		
81397638EP02	Published	Bondwire transformers and their application as power	EP	2010-12-03	2010-12-14	10194851.1	EP2461335	
81397638US04	Granted	Bondwire transformers and their application as power	US	2010-12-14	2011-12-02	13/310293	US20120139640	US9048020
81407638CN02	Granted	High power RF MMIC device for wireless mobile transmitters with high efficiency and linearity in a wide	CN	2011-05-06	2012-05-03	201210135554.3	CN102769431	CN201210135554
81407638DE04	Granted	High power RF MMIC device for wireless mobile transmitters with high efficiency and linearity in a wide	DE	2011 05 06	2011-05-06	11250509.4		DE602011011261
81407638FR05	Granted	High power RF MMIC device for wireless mobile transmitters with high efficiency and linearity in a wide	FR	2011-05-06	2011-05-06	11250509.4		FR2521257
81407638GB06	Granted	High power RF MMIC device for wireless mobile transmitters with high efficiency and linearity in a wide	GB	2011-05-06	2011-05-06	11250509.4		GB2521257
81407638US03	Granted	High power RF MMIC device for wireless mobile transmitters with high efficiency and linearity in a wide	US	2011-05-06	2012-05-03	13/463747	US20130120061	US8710924
81409017DE04	Granted	ESD protection for RF-LDMOS, which can handle negative	DE	2011-04-20	2011-04-20	11163258.4		DE602011003810
81409017FR03	Granted	ESD protection for RF-LDMOS, which can handle negative	FR	2011-04-20	2011-04-20	11163258.4		FR2515334
81409017GB05	Granted	ESD protection for RF-LDMOS, which can handle negative	GB	2011-04-20	2011-04-20	11163258.4		GB2515334
81409017US02	Granted	ESD protection for RF-LDMOS, which can handle negative	US	2011-04-20	2012-04-19	13/450536	US20130107403	US8891214
81413149CN02	Published	N way Doherty amplifier	CN	2011-12-20	2012-12-18	201210551993.2	CN103178787	
81413149DE04	Granted	N way Doherty amplifier	DE	2011-12-20	2011-12-20	11194463.3		DE602011009041
81413149US03	Granted	N way Doherty amplifier	US	2011-12-20	2012-12-04	13/693537	US20130154731	US8928402
81416930CN03	Published	RADIOFREQUENCY AMPLIFIER	CN	2010-12-10	2011-12-09	201110409535.0	CN102570992	
81416930DE05	Granted	RADIOFREQUENCY AMPLIFIER	DE	2010-12-10	2010-12-10	10252098.8	EP2463905	DE602010019218
81416930US04	Granted	RADIOFREQUENCY AMPLIFIER	US	2010-12-10	2011-12-08	13/314752	US20120146723	US8638171
81422760CN02	Published	POWER AMPLIFIER CIRCUIT AND CONTROL METHOD	CN	2012-01-19	2013-01-16	201310015594.9	CN103219956	
81422760EP01	Published	POWER AMPLIFIER CIRCUIT AND CONTROL METHOD	EP		2012-01-19	12151787.4	EP2618481	
81422760US03	Granted	POWER AMPLIFIER CIRCUIT AND CONTROL METHOD	US	2012-01-19	2013-01-16	13/742534	US20130187713	US8736383
81495007CN02	Published	Electronic device comprising RF-LDMOS transistor having	CN	2012-05-14	2013-05-14	201310176747.8	CN103475320	
81495007EP01	Published	Electronic device comprising RF-LDMOS transistor having	EP		2012-05-14	12167901.3	EP2665187	
81495007US03	Granted	Electronic device comprising RF-LDMOS transistor having	US	2012-05-14	2013-05-03	13/887212	US20130307055	US9019671
81495281CN02	Published	Amplifier Circuit	CN	2012-05-17	2013-05-16	201310182184.3	CN103490732	
81495281DE04	Granted	Amplifier Circuit	DE	2012-05-17	2012-05-17	12168446.8		DE602012004305
81495281FR05	Granted	Amplifier Circuit	FR	2012-05-17	2012-05-17	12168446.8		FR2665181
81495281GB05	Granted	Amplifier Circuit	GB	2012-05-17	2012-05-17	12168446.8		GB2665181
81495281US03	Granted	Amplifier Circuit	US	2012-05-17	2013-05-03	13/887182	US20140145791	US9071198
81495610EP01	Published	AN AMPLIFIER CIRCUIT	EP		2012-09-14	12184587.9	EP2709275	
81495610US02	Granted	AN AMPLIFIER CIRCUIT	US	2012-09-14	2013-09-13	14/027109	US20140077877	US9118283
81514336EP01	Published	Dual-Frequency Band High-Power Discrete RF Transistor	EP		2013-05-07	13166882.4	EP2802075	
81514336US02	Published	Dual-Frequency Band High-Power Discrete RF Transistor	US	2013-05-07	2014-05-01	14/267715	US20140333385	
81520716EP01	Published	AMPLIFIER DEVICE	EP		2012-12-18	12197882.9	EP2747134	
81520716US02	Granted	AMPLIFIER DEVICE	US	2012-12-18	2013-12-17	14/109879	US20140167858	US9007129

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81523373EP01	Published	AMPLIFIERS CIRCUIT	EP		2012-10-16	12290346.1	EP2722880	
81523373US02	Published	Extended Video Bandwidth for RF high power amplifiers	US	2012-10-16	2013-10-15	14/054665	US20140179243	
81523723CN04	Published	TRANSMITTER	CN	2012-06-11	2013-06-07	201310225133.4	CN103716059	
81523723EP02	Published	TRANSMITTER	EP	2012-06-11	2013-05-24	13169216.2	EP2675070	
81523723US03	Published	TRANSMITTER	US	2012-06-11	2013-06-11	13/914822	US20130343173	
81524008DE03	Granted	Voltage Controlled Class AB Bias Circuit	DE	2013-01-28	2013-01-28	13290021.8		DE602013002137
81524008FR04	Granted	Voltage Controlled Class AB Bias Circuit	FR	2013-01-28	2013-01-28	13290021.8		FR2760130
81524008GB05	Granted	Voltage Controlled Class AB Bias Circuit	GB	2013-01-28	2013-01-28	13290021.8		GB2760130
81524008US02	Granted	Voltage Controlled Class AB Bias Circuit	US	2013-01-28	2014-01-27	14/164484	US20140210557	US8854143
81524025EP01	Published	AMPLIFIER CIRCUITS	EP		2012-10-16	12290347.9	EP2722981	
81524025US02	Published	AMPLIFIER CIRCUITS	US	2012-10-16	2013-10-15	14/054681	US20140104004	
81524263EP01	Published	Optimum intrinsic Video bandwidth performance for RF	EP		2012-10-17	12290353.7	EP2722881	
81524263US02	Granted	Optimum intrinsic Video bandwidth performance for RF	US	2012-10-17	2013-10-15	14/054705	US20140103447	US9070565
81524439CN03	Published	MARCHAND BALUN AND POWER AMPLIFIER USING THE	CN	2013-06-14	2014-06-10	201410255288.7	CN104241795	
81524439EP01	Published	Novel integrated Marchand balun on very conductive	EP		2013-06-14	13290140.6	EP2814113	
81524439US02	Published	MARCHAND BALUN AND POWER AMPLIFIER USING THE	US	2013-06-14	2014-06-10	14/300435	US20140368270	
81525331CN01	Published	MICROWAVE POWER SOURCE AND METHOD OF	CN		2012-07-05	201210232055.6	CN103533690	
81525331EP02	Published	MICROWAVE POWER SOURCE AND METHOD OF	EP	2012-07-05	2013-05-28	13169425.9	EP2683219	
81525331US03	Published	MICROWAVE POWER SOURCE AND METHOD OF	US	2012-07-05	2013-07-02	13/934022	US20140008357	
81526319DE03	Granted	AMPLIFIER CIRCUIT	DE	2012-11-15	2012-11-15	12192808.9		DE602012009720
81526319FR04	Granted	AMPLIFIER CIRCUIT	FR	2012-11-15	2012-11-15	12192808.9		FR2733742
81526319GB05	Granted	AMPLIFIER CIRCUIT	GB	2012-11-15	2012-11-15	12192808.9		GB2733742
81526319US02	Allowed	AMPLIFIER CIRCUIT	US	2012-11-15	2013-11-14	14/080711	US20140132353	
81526583CN02	Published	Bond wire return path in single chip RF LDMOS power	CN	2013-10-31	2014-10-27	201410584815.9	CN104600099	
81526583EP01	Published	Bond wire return path in single chip RF LDMOS power	EP		2013-10-31	13191204.0	EP2869339	
81526583US03	Published	Bond wire return path in single chip RF LDMOS power	US	2013-10-31	2014-10-27	14/524663	US20150115343	
81529217EP01	Published	Specialized Peaking Transistor for Wideband Doherty	EP		2013-06-26	13173865.0	EP2819304	
81529217US02	Published	DOHERTY AMPLIFIER	US	2013-06-26	2014-06-11	14/301423	US20150002230	
81530995US02	Published	PACKAGE FOR AN INTEGRATED CIRCUIT	US	2012-11-12	2013-11-11	14/077138	US20140131899	
81531947CN02	Published	Air Cavity Package With Slots on Leads	CN	2013-04-24	2014-03-20	201410104360.6	CN104124214	
81531947EP01	Published	Air Cavity Package With Slots on Leads	EP		2013-04-24	13165213.3	EP2797111	
81531947US03	Published	Air Cavity Package With Slots on Leads	US	2013-04-24	2014-04-21	14/257768	US20140318854	
81533301CN02	Published	AMPLIFIER CIRCUITS	CN	2013-08-14	2014-07-28	201410363787.8	CN104378072	
81533301EP01	Published	AMPLIFIER CIRCUITS	EP		2013-08-14	13290190.1	EP2838194	
81533301US03	Granted	AMPLIFIER CIRCUITS	US	2013-08-14	2014-07-28	14/444063	US20150048884	US9041465
81533309CN02	Published	DOHERTY AMPLIFIER	CN	2013-05-23	2014-05-21	201410216104.6	CN104184418	
81533309EP01	Published	Ultra-wide band High Efficiency Doherty PA Architecture	EP		2013-05-23	13168944.0	EP2806557	
81533309US03	Published	DOHERTY AMPLIFIER	US	2013-05-23	2014-05-22	14/284479	US20140347133	
81537984CN03	Published	RF POWER DEVICE	CN	2013-07-25	2014-07-23	201410354016.2	CN104347615	
81537984EP01	Published	Method to reduce distribution effects in packaged	EP		2013-07-25	13178065.2	EP2830089	
81537984US02	Published	RF POWER DEVICE	US	2013-07-25	2014-06-27	14/317030	US20150028955	
81541380CN03	Published	Air cavity moulding with FilmAssistMoulding (FAM) of RF	CN	2013-09-26	2014-09-23	201410490474.9	CN104517926	
81541380CN05	Published	Air cavity moulding with FilmAssistMoulding (FAM) of RF	CN	2013-09-26	2014-09-23	201410488506.1	CN104517925	
81541380EP01	Published	Air cavity moulding with FilmAssistMoulding (FAM) of RF	EP		2013-09-26	13186182.5	EP2854162	
81541380EP02	Published	Air cavity moulding with FilmAssistMoulding (FAM) of RF	EP		2013-09-26	13186180.9	EP2854161	
81541380US04	Published	Air cavity moulding with FilmAssistMoulding (FAM) of RF	US	2013-09-26	2014-09-04	14/476812	US20150084174	
81541380US06	Allowed	Air cavity moulding with FilmAssistMoulding (FAM) of RF	US	2013-09-26	2014-09-05	14/478683	US20150084175	
81543381CN03	Published	High Power Integrated Amplifier	CN	2013-10-31	2014-10-21	201410562192.5	CN104601117	
81543381DE04	Allowed	High Power Integrated Amplifier	DE	2013-10-31	2013-10-31	13290266.9		
81543381EP01	Published	High Power Integrated Amplifier	EP		2013-10-31	13290266.9	EP2869463	
81543381US02	Published	High Power Integrated Amplifier	US	2013-10-31	2014-10-10	14/511307	US20150119107	
81546245US02	Published	Site Scan for Mobile Base stations	US	2013-02-28	2014-02-06	14/174150	US20140243032	
81559481CN02	Published	DOHERTY AMPLIFIER	CN	2013-11-22	2014-10-14	201410540169.6	CN104660176	
81559481EP01	Published	A Wideband, Compact and Very High Power Integrated	EP		2013-11-22	13290292.5	EP2876810	
81559481US03	Published	DOHERTY AMPLIFIER	US	2013-11-22	2014-10-28	14/526069	US20150145601	
81583927CN02	Published	COMBINER CIRCUIT FOR A CLASS-E OUTPHASING POWER	CN	2013-08-14	2014-07-28	201410363089.8	CN104378074	
81583927EP01	Published	Package-Integrated Class-E Chireix Outphasing Power	EP		2013-08-14	13180416.3	EP2838195	
81583927US03	Published	COMBINER CIRCUIT FOR A CLASS-E OUTPHASING POWER	US	2013-08-14	2014-07-28	14/444736	US20150048899	
81588439CN02	Published	A WIDEBAND AMPLIFIER	CN	2013-08-30	2014-08-11	201410392260.8	CN104426483	
81588439EP01	Published	Odd-Mode High Efficiency Amplifier	EP		2013-08-30	13182458.3	EP2843832	
81588439US03	Published	A WIDEBAND AMPLIFIER	US	2013-08-30	2014-07-28	14/444106	US20150061775	
81590641CN03	Published	Novel package for the RF power transistor video	CN	2013-11-29	2014-11-26	201410693875.4	CN104681552	
81590641EP01	Published	Novel package for the RF power transistor video	EP		2013-11-29	13195160.0	EP2879174	
81590641US02	Published	Novel package for the RF power transistor video	US	2013-11-29	2014-10-29	14/527138	US20150156910	
81591142CN02	Application	Means to maximize isolation in Packaged Doherty	CN	2014-03-24	2015-03-18	201510119213.0		
81591142EP01	Application	Means to maximize isolation in Packaged Doherty	EP		2014-03-24	14161346.3		
81591142US03	Allowed	Means to maximize isolation in Packaged Doherty	US	2014-03-24	2015-03-16	14/658479		
81591303EP01	Application	Improvement of the VSWR-ruggedness for RF-LDMOS	EP		2013-11-29	13195174.1	EP2879185	
81594049CN03	Published	Vertical high voltage device integration on isolated silicon	CN	2013-12-20	2014-12-19	201410803328.7	CN104733459	
81594049EP01	Published	Vertical high voltage device integration on isolated silicon	EP		2013-12-20	13199196.0	EP2887387	
81594049US02	Published	Vertical high voltage device integration on isolated silicon	US	2013-12-20	2014-12-18	14/575001	US20150179735	
81613976CN02	Published	High reliability interposer layer for power applications	CN	2013-12-24	2014-12-22	201410806694.8	CN104733418	
81613976EP01	Published	High reliability interposer layer for power applications	EP		2013-12-24	13199587.0	EP2889903	
81613976US03	Published	High reliability interposer layer for power applications	US	2013-12-24	2014-12-05	14/562129	US20150179599	
81616742CN02	Application	A balanced DC bias circuit for RF power transistor	CN	2014-03-04	2015-03-04	201510096397.3		
81616742EP01	Published	A balanced DC bias circuit for RF power transistor	EP		2014-03-04	14157723.9	EP2916356	
81616742US03	Application	A balanced DC bias circuit for RF power transistor	US	2014-03-04	2015-03-02	14/635269		
81617507CN03	Application	Means to minimize distribution effects in packages	CN	2014-05-30	2015-05-21	201510262663.5		
81617507EP02	Application	Means to minimize distribution effects in packages	EP	2014-05-30	2014-08-08	14180430.2		
81617507US04	Application	Means to minimize distribution effects in packages	US	2014-05-30	2015-05-03	14/702740		
81627960CN02	Published	Wideband impedance transforming balun	CN	2014-01-24	2015-01-22	201510032456.0	CN104811150	
81627960EP01	Published	Wideband impedance transforming balun	EP		2014-01-24	14152532.9	EP2899803	
81627960US03	Published	Wideband impedance transforming balun	US	2014-01-24	2015-01-02	14/588581	US20150214919	
81633020CN02	Application	A high Q on-chip bondwire transformer	CN	2014-08-28	2015-08-27			
81633020EP01	Application	A high Q on-chip bondwire transformer	EP		2014-08-28	14182574.5		
81633020US03	Application	A high Q on-chip bondwire transformer	US	2014-08-28	2015-08-07	14/821627		
81633037CN03	Application	Ultra Wide Band Doherty Amplifier	CN	2014-04-15	2015-04-14	201510176684.5		
81633037EP02	Application	ULTRA WIDEBAND DOHERTY AMPLIFIER	EP	2014-04-15	2014-07-03	14175618.9		
81633037US04	Application	Ultra Wide Band Doherty Amplifier	US	2014-04-15	2015-03-25	14/667787		
81633145EP01	Application	Lateral drift HBT with dual-sided RESURF	EP		2015-01-05	15150069.1		
81633545CN02	Application	RADIO FREQUENCY HEATING APPARATUS	CN	2014-06-03	2015-05-29	201510289519.0		
81633545EP01	Application	RADIO FREQUENCY HEATING APPARATUS	EP		2014-06-03	14170871.9		
81633545US03	Application	RADIO FREQUENCY HEATING APPARATUS	US	2014-06-03	2015-05-18	14/715473		
81633699CN02	Application	An innovative wide band RF power transistor	CN	2014-04-15	2015-04-14	2015101750?1.X		
81633699EP01	Application	An innovative wide band RF power transistor	EP		2014-04-15	14164753.7		
81633699US03	Application	An innovative wide band RF power transistor	US	2014-04-15	2015-03-25	14/667860		
81633988EP01	Application	DOHERTY AMPLIFIER	EP		2014-06-18	14173009.3		
81637146EP01	Application	A Multi-band High Efficiency 3-way Integrated Doherty	EP		2014-08-07	14290235.2		
81637146WO02	Application	A Multi-band High Efficiency 3-way Integrated Doherty	WO	2014-08-07	2015-08-07	EP2015/068270		
81642819EP01	Application	An Input Bias Method for RF Power Transistors for	EP		2015-01-28	15152814.8		
81643407EP01	Application	Integrated Outphasing Power Amplifier	EP		2015-04-17	15164060.4		
81644297US01	Application	RF PACKAGE	US		2015-02-12	14/620575		

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81644622EP01	Instructed	Source High LDMOS for RF-LDMOS technology	EP					
81646762EP01	Application	A Multi-band High Efficiency 4-way Doherty Power	EP		2015-02-04	15153816.2		
81647545EP01	Application	A new RF power transistor with compact in-package	EP		2015-05-27	15169491.6		
81649296US01	Application	RF PACKAGE	US		2015-02-12	14/620601		
81649815EP01	Application	Dual Input Power Amplifier(s) based on Quasi Load	EP		2015-06-03	15170516.7		
81652426EP01	Application	A new high density Comb-in-Comb design of Metal-Oxide-	EP		2015-05-28	15169567.3		
81664727EP01	Instructed	Wideband PA cells for high efficiency PA concepts	EP					
81672907EP01	Application	Compact and Very Efficient Multi-way Doherty Power	EP		2015-07-22	15290194.8		
A023082US	Granted	POWER MOSFET WITH METAL GATE IN SOI	US		1995-12-28	08/580409		US5681761
A023083DE	Granted	TRANSISTOR IN SOI WITH MULTIPLE BASE CONTACT	DE	1995-12-28	1996-12-09	96939273.7	EP0812470	DE69626802
A023083USA	Granted	TRANSISTOR IN SOI WITH MULTIPLE BASE CONTACT	US	1995-12-28	1995-12-28	08/934301		US6235601
A023899DE	Granted	SELF-ALIGNED SILICON CARBIDE LMOSFET.	DE	1999-12-21	2000-11-20	00976056.2	EP1177583	DE60045864
A023899JP	Granted	SELF-ALIGNED SILICON CARBIDE LMOSFET.	JP	1999-12-21	2000-11-20	2001-547661		JP4990458
GB040048CN1	Granted	POWER AMPLIFIER OUTPUT IMPEDANCE CONTROL	CN	2004-02-27	2005-02-17	200580005873.0	CN1922788	CN200580005873
GB040048DE	Granted	POWER AMPLIFIER OUTPUT IMPEDANCE CONTROL	DE	2004-02-27	2005-02-17	05702999.3		DE602005022279
GB040048FR	Granted	POWER AMPLIFIER OUTPUT IMPEDANCE CONTROL	FR	2004-02-27	2005-02-17	05702999.3		FR1719250
NL000549DE	Granted	MERGED ESD DIODE IN POWER TRANSISTOR	DE	2000-10-08	2001-09-26	01986798.5		DE60133302
NL000549FR	Granted	MERGED ESD DIODE IN POWER TRANSISTOR	FR	2000-10-08	2001-09-26	01986798.5		FR1327266
NL000549GB	Granted	MERGED ESD DIODE IN POWER TRANSISTOR	GB	2000-10-08	2001-09-26	01986798.5		GB1327266
NL000549US	Granted	MERGED ESD DIODE IN POWER TRANSISTOR	US	2000-10-08	2001-10-05	09/972576	US20020040996	US6917077
NL010012DE08	Granted	POWER TRANSISTOR WITH INTERNAL LOW-PASS AND	DE	2001-01-18	2001-12-17	01273315.0		DE60136961
NL010012FR07	Granted	POWER TRANSISTOR WITH INTERNAL LOW-PASS AND	FR	2001-01-18	2001-12-17	01273315.0		FR1356521
NL010012US	Granted	POWER TRANSISTOR WITH INTERNAL LOW-PASS AND	US	2001-01-18	2002-01-15	10/047030	US20020109203	US6646321
NL010706CN	Granted	RF POWER AMPLIFIER CIRCUIT	CN	2001-10-16	2002-10-02	02820426.3	CN1572055	CN02820426
NL010706US	Granted	RF POWER AMPLIFIER CIRCUIT	US	2001-10-16	2002-10-11	10/270345	US20030087626	US6990323
NL020058CN	Granted	INSHIN DECOUPLING AND POWER SUPPLY	CN	2002-01-24	2003-01-23	03802644.9	CN1623232	CN03802644
NL020058US	Granted	INSHIN DECOUPLING AND POWER SUPPLY	US	2002-01-24	2003-01-23	10/502155	US20050083118	US7119613
NL020103CN	Granted	POWER TRANSISTOR HARMONIC TERMINATION	CN	2002-02-01	2003-01-30	03802894.8	CN1625834	CN03802894
NL020103US	Granted	POWER TRANSISTOR HARMONIC TERMINATION	US	2002-02-01	2003-01-30	10/502790	US20050083723	US7119623
NL020250CN	Granted	DEVICE WITH HARMONIC CIRCUIT DIRECTLY AT DIE AREA	CN	2002-03-21	2003-03-20	03806524.X	CN1643685	CN03806524
NL020250US	Granted	DEVICE WITH HARMONIC CIRCUIT DIRECTLY AT DIE AREA	US	2002-03-21	2003-03-20	10/507992	US20050104679	US7138872
NL020752CN	Granted	HIGH POWER DOHERTY AMPLIFIER	CN	2002-08-19	2003-07-18	03819374.4	CN1675826	CN03819374
NL020752DE09	Granted	HIGH POWER DOHERTY AMPLIFIER	DE	2002-08-19	2003-07-18	03787936.8		DE60338475
NL020752FR08	Granted	HIGH POWER DOHERTY AMPLIFIER	FR	2002-08-19	2003-07-18	03787936.8		FR1532731
NL020752US	Granted	HIGH POWER DOHERTY AMPLIFIER	US	2002-08-19	2003-07-18	10/524571	US20050231278	US7078976
NL020886US1	Granted	PRESERVING LINEARITY OF A POWER AMPLIFIER	US	2002-09-17	2003-08-04	10/527775	US20050270105	US7482873
NL020964US	Granted	ADAPTIVE CONTROL OF QUIESCENT CURRENT FOR	US	2002-10-03	2003-09-12	10/529666	US20060066403	US7157974
NL021045US	Granted	PREDISTORTION LINEARIZER	US	2002-10-22	2003-10-17	10/531932	US20060033568	US7332961
NL021048US	Granted	INTEGRATED TEMPERATURE COMPENSATED BIAS CIRCUIT	US	2002-10-30	2003-09-22	10/532929	US20060087377	US7286016
NL021429JP1	Granted	POWER AMPLIFIER WITH BIAS FEEDBACK	JP	2002-12-19	2003-11-20	2004-561753		JP4744881
NL021429US1	Granted	POWER AMPLIFIER WITH BIAS FEEDBACK	US	2002-12-19	2003-11-20	10/539383	US20060145766	US7477106
NL030296DE1	Granted	ADAPTIVE BIASING OF A POWER AMPLIFIER VIA A SWITCH	DE	2003-03-27	2004-03-22	04722373.0		DE602004001684
NL030296US1	Granted	ADAPTIVE BIASING OF A POWER AMPLIFIER VIA A SWITCH	US	2003-03-27	2004-03-22	10/550340	US20060246857	US7392023
NL030296US2	Granted	ADAPTIVE BIASING OF A POWER AMPLIFIER VIA A SWITCH	US	2003-03-27	2004-03-22	12/021958	US20080139129	US7483681
NL030460CN1	Granted	LOW-DISTORTION FET WITH MULTIPLE THRESHOLDS	CN	2003-05-02	2004-04-28	200480011788.0	CN1781193	CN200480011788
NL030460US1	Granted	LOW-DISTORTION FET WITH MULTIPLE THRESHOLDS	US	2003-05-02	2004-04-28	10/555054	US20060231905	US8357979
NL030877CN1	Granted	COMPACT IMPEDANCE TRANSFORMATION CIRCUIT	CN	2003-07-23	2004-07-13	200480021013.1	CN1826671	CN200480021013
NL030877DE	Granted	COMPACT IMPEDANCE TRANSFORMATION CIRCUIT	DE	2003-07-23	2004-07-13	04744561.4	EP1652198	DE602004029469
NL030877FR	Granted	COMPACT IMPEDANCE TRANSFORMATION CIRCUIT	FR	2003-07-23	2004-07-13	04744561.4		FR1652198
NL030877GB	Granted	COMPACT IMPEDANCE TRANSFORMATION CIRCUIT	GB	2003-07-23	2004-07-13	04744561.4		GB1652198
NL030877US1	Granted	COMPACT IMPEDANCE TRANSFORMATION CIRCUIT	US	2003-07-23	2004-07-13	10/565935	US20080055015	US7443264
NL031066US1	Granted	LDMOS WITH STEPPED SHIELD AND HDD	US	2003-08-27	2004-08-24	10/569171	US20070007591	US7521768
NL040770CN1	Granted	DOHERTY AMPLIFIER	CN	2004-06-29	2005-06-28	200580022092.2	CN1977447	CN200580022092
NL040770DE03	Granted	DOHERTY AMPLIFIER	DE	2004-06-29	2005-06-28	05751755.9		DE602005032513
NL040770FR02	Granted	DOHERTY AMPLIFIER	FR	2004-06-29	2005-06-28	05751755.9		FR1763921
NL040770US1	Granted	DOHERTY AMPLIFIER	US	2004-06-29	2005-06-28	11/631206	US20090212858	US7884668
NL041358DE	Granted	CURRENT LIMITING AMPLIFIER	DE	2004-11-29	2005-11-23	05807212.5		DE602005029792
NL041358US1	Granted	CURRENT LIMITING AMPLIFIER	US	2004-11-29	2005-11-23	11/720321	US20090170454	US7873335
NL041448CN1	Granted	POWER SENSOR OF PA AS A BOND WIRE STRUCTURE	CN	2004-12-21	2005-12-15	200580043625.5		CN200580043625
NL041448DE03	Granted	POWER SENSOR OF PA AS A BOND WIRE STRUCTURE	DE	2004-12-21	2005-12-15	05825463.2		DE602005039834
NL041448FR02	Granted	POWER SENSOR OF PA AS A BOND WIRE STRUCTURE	FR	2004-12-21	2005-12-15	05825463.2		FR1831995
NL041448JP1	Granted	POWER SENSOR OF PA AS A BOND WIRE STRUCTURE	JP	2004-12-21	2005-12-15	2007-547738		JP4658141
NL041448US1	Published	POWER SENSOR OF PA AS A BOND WIRE STRUCTURE	US	2004-12-21	2005-12-15	11/722521	US20100188164	